

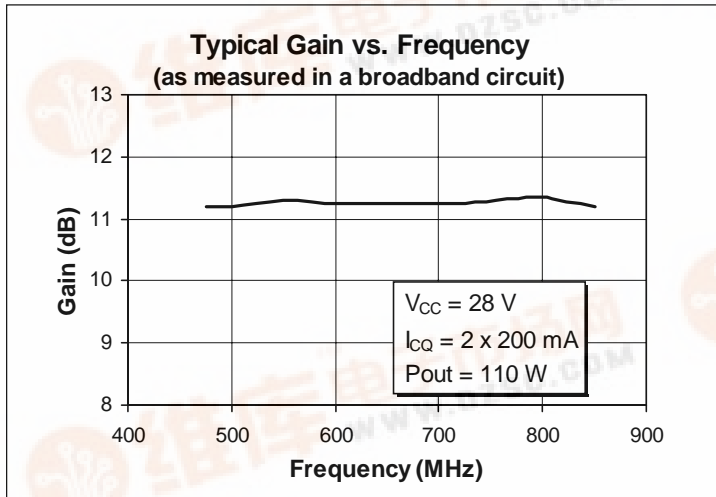


PTB 20101 175 Watts P-Sync, 470–860 MHz UHF TV Power Transistor

Description

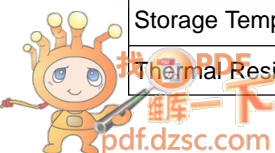
The 20101 is a class AB, NPN, common emitter UHF TV power transistor intended for 28 Vdc operation from 470 to 860 MHz. It is rated at 175 watts P-sync minimum output power. Ion implantation, nitride surface passivation and gold metallization are used to ensure excellent device reliability. 100% lot traceability is standard.

- 28 Volt, 860 MHz Characteristics
 - Output Power = 175 Watts P-Sync
 - Output Power = 110 (CW)
 - Gain = 10.0 dB Min
- 55% Collector Efficiency at 110 Watts
- Class AB Characteristics
- Gold Metallization
- Silicon Nitride Passivated



Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CER}	40	Vdc
Collector-Base Voltage	V_{CBO}	65	Vdc
Emitter-Base Voltage (collector open)	V_{EBO}	4.0	Vdc
Collector Current (continuous)	I_C	20	Adc
Total Device Dissipation at $T_{flange} = 25^\circ\text{C}$ Above 25°C derate by	P_D	330 1.89	Watts W/ $^\circ\text{C}$
Storage Temperature Range	T_{STG}	-40 to +150	$^\circ\text{C}$
Thermal Resistance ($T_{flange} = 70^\circ\text{C}$)	$R_{\theta JC}$	0.53	$^\circ\text{C/W}$



Electrical Characteristics (100% Tested)

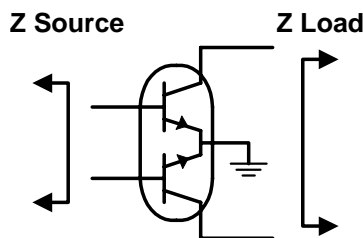
Characteristic	Conditions	Symbol	Min	Typ	Max	Units
Breakdown Voltage C to E	$I_B = 0\text{ A}$, $I_C = 100\text{ mA}$	$V_{(BR)CEO}$	25	30	—	Volts
Breakdown Voltage C to E	$V_{BE} = 0\text{ V}$, $I_C = 100\text{ mA}$	$V_{(BR)CES}$	55	70	—	Volts
Breakdown Voltage E to B	$I_C = 0\text{ A}$, $I_E = 5\text{ mA}$	$V_{(BR)EBO}$	3.5	5	—	Volts
DC Current Gain	$V_{CE} = 5\text{ V}$, $I_C = 1\text{ A}$	h_{FE}	20	50	100	—
Output Capacitance (per side)	$V_{CB} = 28\text{ V}$, $I_E = 0\text{ A}$, $f = 1\text{ MHz}$	C_{ob}	—	85	—	pF

RF Specifications (100% Tested)

Characteristic	Symbol	Min	Typ	Max	Units
Output Power (P-Sync) ($V_{CC} = 28\text{ Vdc}$, $I_{CQ} = 200\text{ mA}$ per side, $f = 860\text{ MHz}$)	P_{out}	175	—	—	Watts
Gain ($V_{CC} = 28\text{ Vdc}$, $P_{out} = 110\text{ W}$, $I_{CQ} = 200\text{ mA}$ per side, $f = 860\text{ MHz}$)	G_{pe}	10.0	11	—	dB
Collector Efficiency ($V_{CC} = 28\text{ Vdc}$, $P_{out} = 110\text{ W}$, $I_{CQ} = 200\text{ mA}$ per side, $f = 860\text{ MHz}$)	η_C	55	58	—	%
Load Mismatch Tolerance ($V_{CC} = 28\text{ Vdc}$, $P_{out} = 175\text{ W}$, $I_{CQ} = 200\text{ mA}$ per side, $f = 860\text{ MHz}$ —all phase angles at frequency of test)	Ψ	—	—	5:1	—

Impedance Data (data shown for fixed-tuned broadband circuit)

($V_{CC} = 28\text{ Vdc}$, $P_{out} = 110\text{ W}$, $I_{CQ} = 200\text{ mA}$ per side)



Frequency MHz	Z Source		Z Load	
	R	jX	R	jX
450	0.4	-1.0	2.0	0.3
550	0.5	-1.3	1.6	0.0
650	0.7	-1.8	1.3	0.0
750	1.8	-2.0	1.0	-0.8
850	2.7	-0.5	0.9	-1.2

